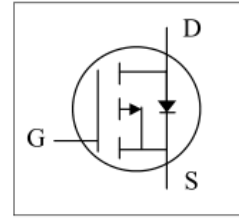


30V P-Channel Enhancement Mode MOSFET

Description

The AO4435 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

$V_{DS} = -30V$ $I_D = -12A$

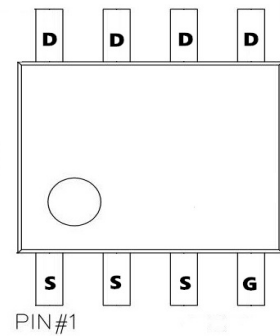
$R_{DS(ON)} < 20m\Omega$ @ $V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply



Absolute Maximum Ratings ($T_c=25^{\circ}C$ unless otherwise noted)

| Symbol | Parameter | Rating | Units |
|-----------------------|---|------------|----------------|
| V_{DS} | Drain-Source Voltage | - 30 | V |
| V_{GS} | Gate-Source Voltage | ± 20 | V |
| $I_D@T_A=25^{\circ}C$ | Drain Current ³ , V_{GS} @ 10V | -12 | A |
| $I_D@T_A=70^{\circ}C$ | Drain Current ³ , V_{GS} @ 10V | -10 | A |
| I_{DM} | Pulsed Drain Current ¹ | -50 | A |
| $P_D@T_A=25^{\circ}C$ | Total Power Dissipation | 2.5 | W |
| | Linear Derating Factor | 0.02 | W/ $^{\circ}C$ |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^{\circ}C$ |
| T_J | Operating Junction Temperature Range | -55 to 150 | $^{\circ}C$ |
| R_{thj-a} | Maximum Thermal Resistance, Junction-ambient ³ | 50 | $^{\circ}C/W$ |

30V P-Channel Enhancement Mode MOSFET
Electrical Characteristics@T_j=25°C(unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|---------------------|--|---|------|------|------|-------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =-250uA | -30 | - | - | V |
| R _{DS(ON)} | Static Drain-Source On-Resistance ² | V _{GS} =-10V, I _D =-7A | - | 15 | 20 | mΩ |
| | | V _{GS} =-4.5V, I _D =-5A | - | 25 | 32 | mΩ |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =-250uA | -1 | - | -3 | V |
| g _{fs} | Forward Transconductance | V _{DS} =-10V, I _D =-7A | - | 16 | - | S |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =-24V, V _{GS} =0V | - | - | -30 | uA |
| I _{GSS} | Gate-Source Leakage | V _{GS} =±20V, V _{DS} =0V | - | - | ±100 | nA |
| Q _g | Total Gate Charge | I _D =-7A | - | 18 | 29 | nC |
| Q _{gs} | Gate-Source Charge | V _{DS} =-24V | - | 3 | - | nC |
| Q _{gd} | Gate-Drain ("Miller") Charge | V _{GS} =-4.5V | - | 10 | - | nC |
| t _{d(on)} | Turn-on Delay Time | V _{DS} =-15V | - | 8 | - | ns |
| t _r | Rise Time | I _D =-1A | - | 6.6 | - | ns |
| t _{d(off)} | Turn-off Delay Time | R _G =3.3Ω | - | 44 | - | ns |
| t _f | Fall Time | V _{GS} =-10V | - | 34 | - | ns |
| C _{iss} | Input Capacitance | V _{GS} =0V | - | 1175 | 1690 | pF |
| C _{oss} | Output Capacitance | V _{DS} =-25V | - | 195 | - | pF |
| C _{rss} | Reverse Transfer Capacitance | f=1.0MHz | - | 190 | - | pF |
| V _{SD} | Forward On Voltage ² | I _S =-2.1A, V _{GS} =0V | - | - | -1.2 | V |
| t _{rr} | Reverse Recovery Time | I _S =-7A, V _{GS} =0V, dI/dt=100A/μs | - | 28 | - | ns |
| Q _{rr} | Reverse Recovery Charge | | - | 18 | - | nC |

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board, t_l≤10sec ; 125 °C/W when mounted on Min. cop

30V P-Channel Enhancement Mode MOSFET

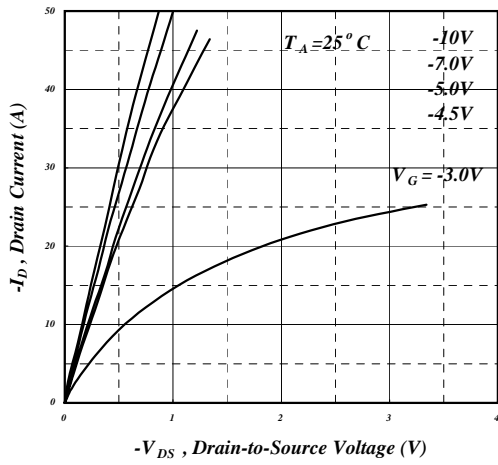


Fig 1. Typical Output Characteristics

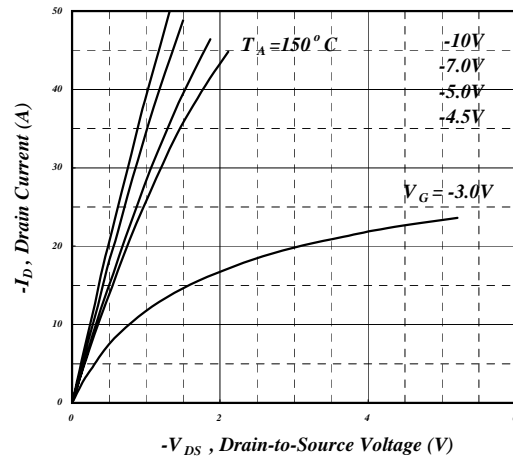


Fig 2. Typical Output Characteristics

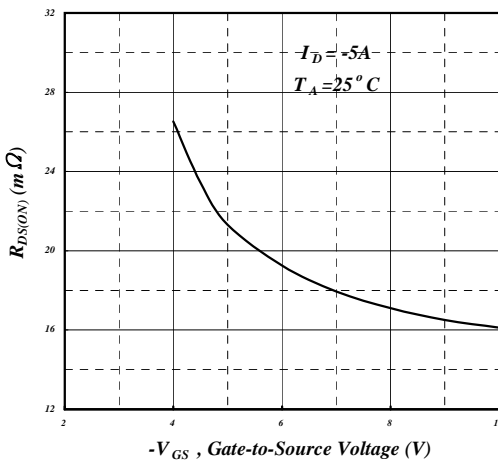


Fig 3. On-Resistance v.s. Gate Voltage

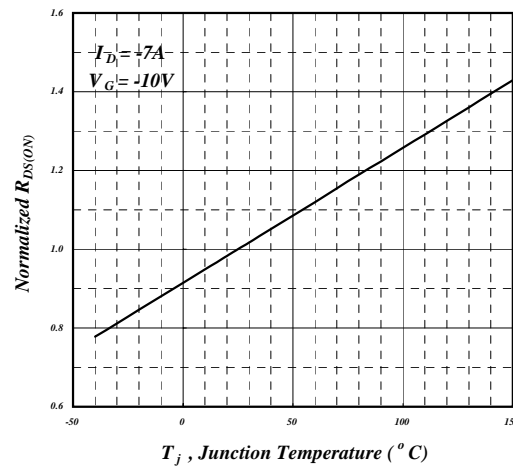


Fig 4. Normalized On-Resistance v.s. Junction Temperature

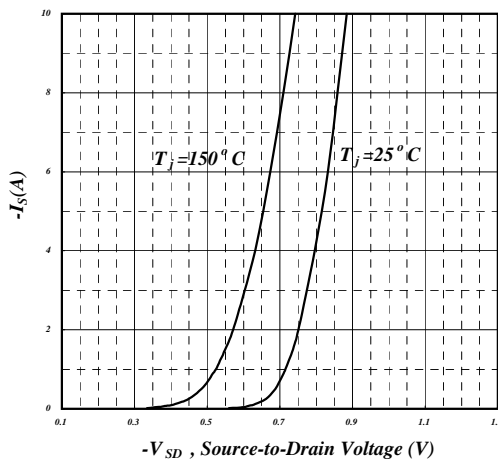


Fig 5. Forward Characteristic of Reverse Diode

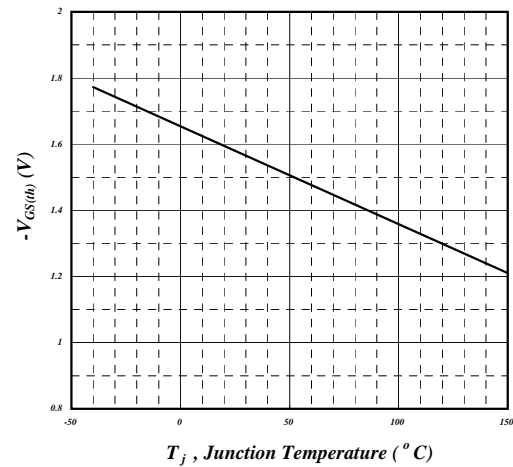


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

30V P-Channel Enhancement Mode MOSFET

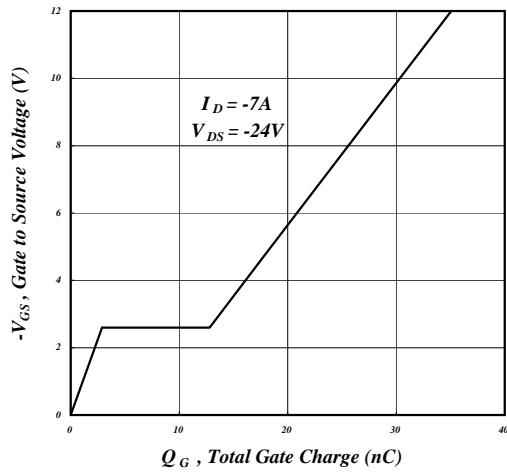


Fig 7. Gate Charge Characteristics

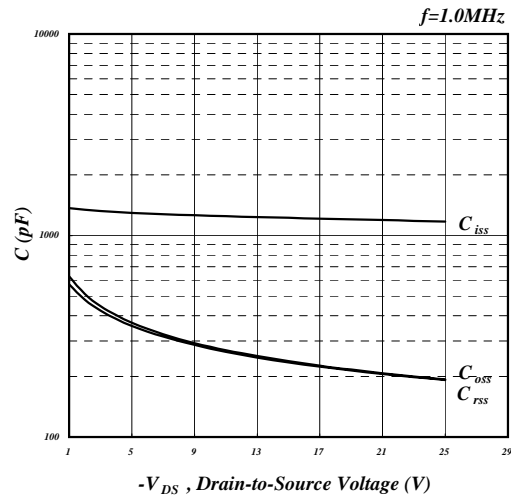


Fig 8. Typical Capacitance Characteristics

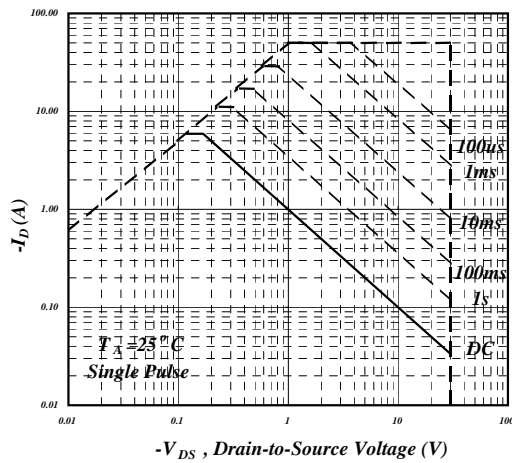


Fig 9. Maximum Safe Operating Area

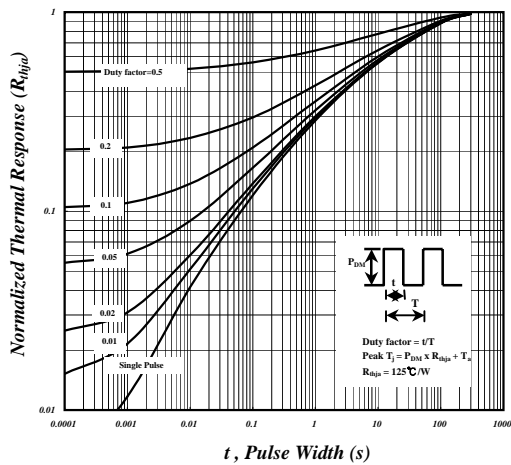


Fig 10. Effective Transient Thermal Impedance

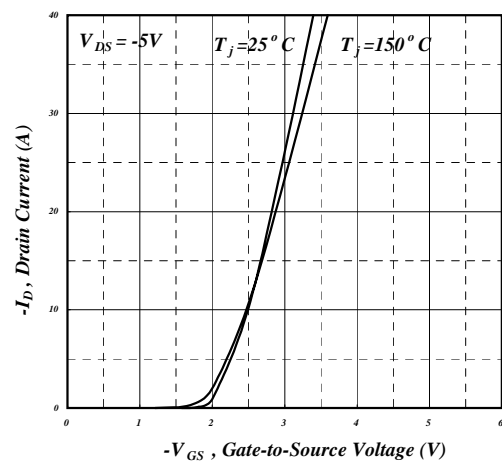


Fig 11. Transfer Characteristics

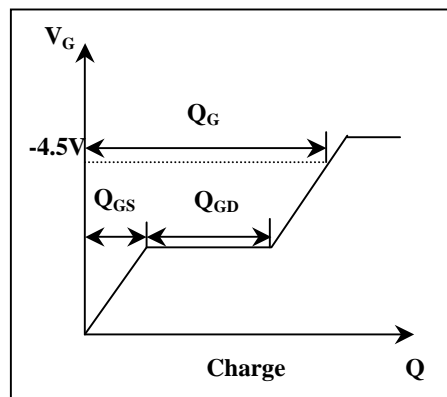
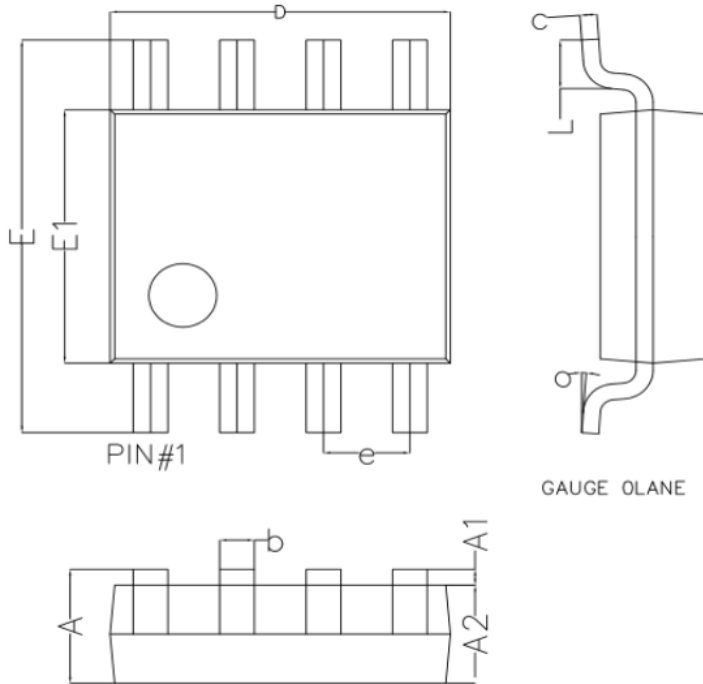


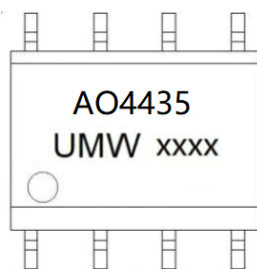
Fig 12. Gate Charge Circuit

SOP8 Package outline



| Symbol | Dim in mm | | |
|--------|-------------|-------|--------|
| | Min | Nor | Max |
| A | 1.350 | 1.550 | 1.750 |
| A1 | 0.100 | 0.175 | 0.250 |
| A2 | 1.350 | 1.450 | 1.550 |
| b | 0.330 | 0.420 | 0.510 |
| c | 0.170 | 0.210 | 0.250 |
| D | 4.800 | 4.900 | 5.000 |
| e | 1.270 (BSC) | | |
| E | 5.800 | 6.000 | 6.200 |
| E1 | 3.800 | 3.900 | 4.000 |
| L | 0.400 | 0.835 | 1.2700 |
| o | 0° | 4° | 8° |

Marking



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